

**INVESTIGATION OF INSULATOR OXIDATION TYPE AND  
THICKNESS ON THE CAPACITOR ELECTRICAL CHARACTERISTIC**

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**MAY 2010**

This Final Year Project Report entitled “**Investigation of Insulator Oxidation Type on the Capacitor Electrical Characteristic**” was submitted by Mohd Nashriq Shauket Mohd Nasir, in partial fulfillment of the requirements for the Degree of Bachelor of Science (Hons.) Industrial Physics, in the Faculty of Applied Sciences, and was approved by



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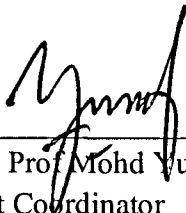
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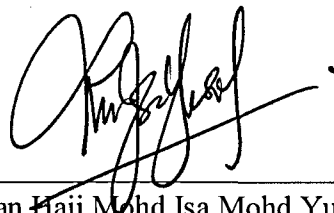
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Date: 12 MAY 2010

## TABLE OF CONTENTS

	<b>Page</b>
<b>ACKNOWLEDGEMENTS</b>	iii
<b>TABLE OF CONTENTS</b>	iv
<b>LIST OF TABLES</b>	vii
<b>LIST OF FIGURES</b>	viii
<b>LIST OF ABBREVIATIONS</b>	ix
<b>ABSTRACT</b>	x
<b>ABSTRAK</b>	xi
<b>CHAPTER 1 INTRODUCTION</b>	
1.1 Background	1
1.1.1 What is Silicon?	1
1.1.2 What is Semiconductor?	2
1.1.3 What is Capacitor?	2
1.2 Objective of Study	3
1.3 Significance of Study	3
1.4 Problem statement	4
<b>CHAPTER 2 LITERATURE REVIEW</b>	
2.1 Fundamental and Equation	6
2.2 Structure and Principle Operation of MOS Capacitor	7
2.2.1 Accumulation	9
2.2.2 Depletion	9
2.2.3 Inversion	9
2.3 Capacitance – Voltage characteristic (C-V)	10
2.3.1 Capacitance-voltage measurement at low frequency	12
2.3.2 Capacitance-voltage measurement at high frequency	13
2.4 Previous study for insulator type and thickness	13
2.4.1 Insulator material type	14
2.5 Application of insulator oxidation in technology	16
<b>CHAPTER 3 METHODOLOGY</b>	
3.1 Equipment, materials, chemicals	17
3.1.1 Equipment	17
3.1.2 Chemical, gases	19

## ABSTRACT

MOS capacitors with SiO<sub>2</sub> and various thickness of insulator (dielectric) layer were fabricated and characterized. SiO<sub>2</sub> films were physical characterized by F20 Thin Film Analyzer, Four Point Probe. Capacitance-voltage measurements were utilized to obtain, the effective dielectric constant, effective oxide thickness, threshold voltage, interface quality, flatband voltage and sheet resistance. Theoretical and experimental studies on MOS capacitor built on p-type Si substrates with different SiO<sub>2</sub> thickness (1000 Å, 2000 Å, 3000 Å, 4000 Å), have been carried out by wet and dry oxidation. The oxide capacitance and electrical properties are determined to be a function of both the oxide thickness and at fixed gate area. Results shows that dry oxidation produce high quality of insulator layer than wet oxidation. As oxide thickness increased, threshold and flatband voltage increased linearly.

**Key words:** Dielectric thickness; Capacitance-Voltage measurement; Electrical properties of MOS capacitor; Oxide thickness variation; Growth by wet and dry oxidation.

## CHAPTER 1

### INTRODUCTION

#### 1.1 Background

##### 1.1.1 What is silicon?

Silicon (Si) has many uses within the field of semiconductors. Elemental silicon is the main component of most devices, most importantly integrated circuits or microchips. Silicon is widely used in semiconductors because it remains a semiconductor at higher temperatures than other materials and because its native oxide is easily grown and forms a better semiconductor/dielectric interface than almost all other material combinations. Doping Silicon with other elements adjusts its electrical response by controlling the number and charge of current carriers. Such control is necessary for transistors, solar cells, microprocessors, semiconductor detectors and other semiconductor devices which are used in electronics and other high-tech applications.

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